# **Monolithic Amplifier**

## DC-6 GHz

#### **Product Features**

- High Gain, 24 dB typ. at 100 MHz
- High IP3, 37 dBm typ. at 100 MHz
- High Pout, P1dB 20.5 dBm typ. at 100 MHz
- Fixed 5V operation
- Unconditionally stable
- Transient protected
- Excellent ESD Protection
- Aqueous washable
- Protected by US patent 6,943,629



**GVA-84+** 

CASE STYLE: DF782 PRICE: \$1.82 ea. QTY. (25)

+ RoHS compliant in accordance with EU Directive (2002/95/EC)

The +Suffix has been added in order to identify RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications.

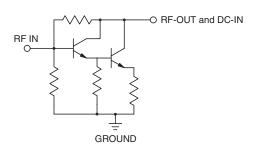
## **Typical Applications**

- Base station infrastructure
- Portable Wireless
- CATV & DBS
- MMDS & Wireless LAN

## **General Description**

GVA-84+ (RoHS compliant) is a wideband amplifier offering high dynamic range. Lead finish is SnAgNi. It has repeatable performance from lot to lot and is enclosed in a SOT-89 package. It uses patented Transient Protected Darlington configuration and is fabricated using InGaP HBT technology. Expected MTBF is 1200 years at 85°C case temperature. GVA-84+ is designed to be rugged for ESD and supply switch-on transients.

#### simplified schematic and pin description





Function	Pin Number	Description
RF IN	1	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.
RF-OUT and DC-IN	3	RF output and bias pin. DC voltage is present on this pin; therefore a DC blocking capacitor is necessary for proper operation. An RF choke is needed to feed DC bias without loss of RF signal due to the bias connection, as shown in "Recommended Application Circuit".
GND	2,4	Connections to ground. Use via holes as shown in "Suggested Layout for PCB Design" to reduce ground path inductance for best performance.







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Electrical Specifications at 25°C and 5V, unless noted

Parameter		Min.	Тур.	Max.	Units	Cpk
Frequency Range <sup>(1)</sup>		DC		6	GHz	
Gain	f=0.1 GHz	22.9	24.1	25.3		≥1.5
	f=1 GHz		21.7			
	f=2 GHz	17.4	18.4	19.9	4D	
	f=3 GHz		16.0		dB	
	f=4 GHz	13.8	14.6	16.3		
	f=6 GHz		12.5			
Magnitude of Gain Variation versus Temperature	f=0.1 GHz		0.0004			
(values are negative)	f=1 GHz		0.0021			
	f=2 GHz		0.0032	0.006	dB/°C	
	f=3 GHz		0.0044		42, 0	
	f=4 GHz		0.0058			
	f=6 GHz		0.0131			
Input Return Loss	f=0.1 GHz		22.9			
	f=1 GHz		20.6			
	f=2 GHz	15	18.5		dB	
	f=3 GHz		18.1			
	f=4 GHz		19.1			
	f=6 GHz		17.9			
Output Return Loss	f=0.1 GHz		23.3			
	f=1 GHz f=2 GHz	6	10.7 7.7			
	f=3 GHz	0	7.7		dB	
	f=4 GHz		7.1			
	f=6 GHz		6.3			
Reverse Isolation	f=2 GHz		26.5		dB	
	f=0.1 GHz	19.4	20.4		ub.	≥1.5
Output Power @1 dB compression	f=1 GHz	19.5	20.5			_1.0
	f=2 GHz	19.6	20.6			
	f=3 GHz		21.0		dBm	
	f=4 GHz		19.9			
	f=6 GHz		17.0			
Saturated Output Power	f=0.1 GHz		21.7			
(at 3dB compression)	f=1 GHz		22.3			
. ,	f=2 GHz		22.3			
	f=3 GHz		22.2		dBm	
	f=4 GHz		21.0			
	f=6 GHz		18.9			
Output IP3	f=0.1 GHz	33	36.7			≥1.5
	f=1 GHz	32.2	35.8			
	f=2 GHz	32.9	36.6		dBm	
	f=3 GHz		35.8		dbiii	
	f=4 GHz		34.9			
	f=6 GHz		33.0			
Noise Figure	f=0.1 GHz		5.5	6.5		≥1.5
	f=1 GHz		5.6			
	f=2 GHz		5.5	6.5	dB	
	f=3 GHz		5.5			
	f=4 GHz		5.6	6.6		
Onesia Delesi	f=6 GHz		6.2			
Group Delay	f=2 GHz	4.0	94	F 0	psec	
Device Operating Current		4.8	5.0 108	5.2 130	V m^	
Device Operating Current		85	-	130	mA	
Device Current Variation vs. Temperature at 5V			61.8		μΑ/°C	
Device Current Variation vs Voltage at 25°C Thermal Resistance, junction-to-case <sup>(2)</sup>			0.058		mA/mV °C/W	
memai nesistance, junction-to-case <sup>(-)</sup>			64		-0/00	

<sup>(1)</sup> Guaranteed specification DC-6 GHz. Low frequency cut off determined by external coupling capacitors.

## (2)Case is defined as ground leads.

## **Absolute Maximum Ratings**

Parameter	Ratings			
Operating Temperature <sup>(3)</sup>	-45°C to 85°C			
Storage Temperature	-65°C to 150°C			
Operating Current	160mA			
Power Dissipation	1W			
Input Power	13dBm			

Note: Permanent damage may occur if any of these limits are exceeded. These ratings are not intended for continuous normal operation. (3)Based on typical case temperature rise 10°C above ambient.





## **Product Marking**



#### **Additional Detailed Technical Information**

Additional information is available on our web site. To access this information enter the model number on our web site home page.

Performance data, graphs, s-parameter (S2P FILES) data set (.zip file)

Case Style: DF782 (SOT 89)

Plastic package, exposed paddle, lead finish: tin/silver/nickel

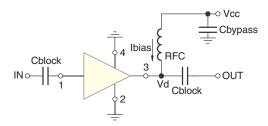
Tape & Reel: F55

Suggested Layout for PCB Design: PL-255

Evaluation Board: TB-410-84+

**Environmental Ratings: ENV08T2** 

## **Recommended Application Circuit**



Test Board includes case, connectors, and components soldered to PCB





## **ESD Rating**

Human Body Model (HBM): Class 1C (1000v to < 2000v) in accordance with ANSI/ESD STM 5.1 - 2001

Machine Model (MM): Class M2 (100V to < 200V) in accordance with ANSI/ESD STM 5.2 - 1999

### **MSL Rating**

Moisture Sensitivity: MSL1 in accordance with IPC/JEDECJ-STD-020C

No.	Test Required	Condition	Standard	Quantity
1	Visual Inspection	Low Power Microscope Magnification 40x	MIP-IN-0003 (MCT spec)	45 units
2	Electrical Test	Room Temperature	SCD (MCL spec)	45 units
3	SAM Analysis	Less than 10% growth in term of delamination	J-Std-020C (Jedec Standard)	45 units
4	Moisture Sensitivity Level 1	Bake at 125°C for 24 hours Soak at 85°C/85%RH for 168 hours Reflow 3 cycles at 260°C peak	J-Std-020C (Jedec Standard)	45 units

#### **MSL Test Flow Chart**

